SCS215AE

SiC Schottky Barrier Diode

Datasheet

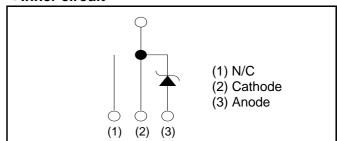
V_R	650V
I _F	15A
Q_{C}	23nC

● Outline TO-247 (1) (2) (3)

Features

- 1) Shorter recovery time
- 2) Reduced temperature dependence
- 3) High-speed switching possible

•Inner circuit



Applications

- PFC Boost Topology
- Secondary Side Rectification
- Data Center
- PV Power Conditioners

●Packaging specifications

	aging opcomoduono	
	Packaging	Tube
	Reel size (mm)	-
Type	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Packing code	С
	Marking	SCS215AE

•Absolute maximum ratings $(T_i = 25^{\circ}C)$

Parameter		Symbol Value		Unit	
Reverse voltage (repetitive peak)		V _{RM} 650		V	
Reverse voltage (De	C)	V_R	650	V	
Continuous forward	current (T _c = 134°C)	I _F	I _F 15/30		
Surge non-	PW=10ms sinusoidal, T _j =25°C		52	А	
repetitive forward	PW=10ms sinusoidal, T _j =150°C I _{FSM}		41	А	
current	PW=10μs square, T _j =25°C		200	А	
Repetitive peak forward current		I _{FRM}	65 *1	А	
PW=10ms, T _j =25°C		$\int i^2 dt$	13	A ² s	
i ² t value PW=10ms, T _j =150°C		J i⁻dt	8.4	A ² s	
Total power disspation		P_{D}	110 *2	W	
Junction temperature		T _j	175	°C	
Range of storage temperature		T _{stg}	-55 to +175	°C	

^{*1} T_c=100°C, T_i=150°C, Duty cycle=10% *2 T_c=25°C

●Electrical characteristics (T_j = 25°C)

Parameter Sym	Symbol	Symbol Conditions -	Values			Linit
	Symbol		Min.	Тур.	Max.	Unit
DC blocking voltage	V_{DC}	I _R =3.0mA	650	-	-	V
	V _F	I _F =15A,T _j =25°C	-	1.35	1.55	V
Forward voltage		I _F =15A,T _j =150°C	-	1.55	-	V
		I _F =15A,T _j =175°C	-	1.63	-	V
Reverse current	I _R	V _R =600V,T _j =25°C	-	3	300	μΑ
		V _R =600V,T _j =150°C	-	45	-	μΑ
		V _R =600V,T _j =175°C	-	105	-	μΑ
Total capacitance	С	V _R =1V,f=1MHz	-	550	-	pF
		V _R =600V,f=1MHz	-	56	-	pF
Total capacitive charge	Q _C	V _R =400V,di/dt=350A/μs	-	23	-	nC
Switching time	t _C	V _R =400V,di/dt=350A/μs	-	18	-	ns

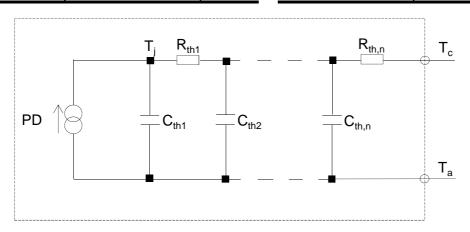
Thermal characteristics

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Offic
Thermal resistance	R _{th(j-c)}	-	-	1.1	1.3	°C/W

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	2.90E-01	
R _{th2}	8.03E-01	K/W
R _{th3}	8.54E-03	

Symbol	Value	Unit
C _{th1}	2.33E-03	
C _{th2}	8.15E-03	Ws/K
C _{th3}	5.82E-01	



•Electrical characteristic curves

Fig.1 V_F - I_F Characteristics

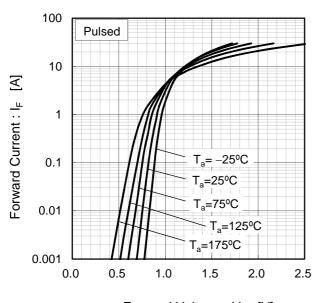
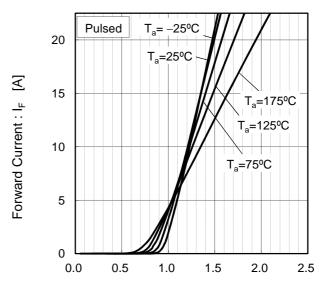


Fig.2 V_F - I_F Characteristics



Forward Voltage : V_F [V]

Forward Voltage : V_F [V]

Fig.3 V_R - I_R Characteristics

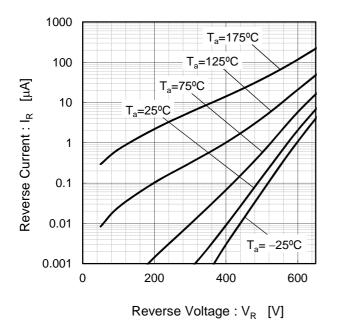
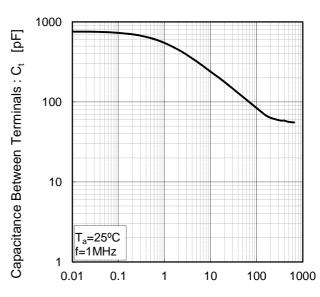
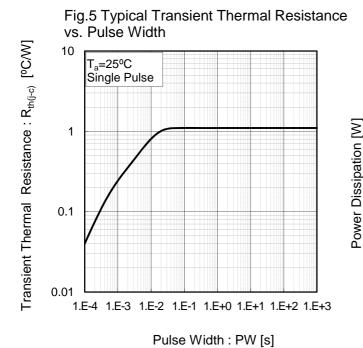


Fig.4 V_R - C_t Characteristics



Reverse Voltage : V_R [V]

•Electrical characteristic curves



140 120 100 80 60 40 20 0 25 50 75 100 125 150 175

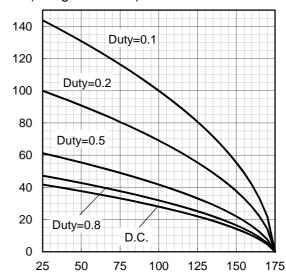
Fig.6 Power Dissipation

Fig.7*3 Maximum peak forward current derating curve I_P - T_c 140 120 Peak Forward Current : Ip [A] Duty=0.1 100 Duty=0.2 80 60 Duty=0.5 40 20 Duty=0.8 D.C. 0 25 50 75 100 125 150 175

Case Temperature : T_c [°C] *3 Based on max Vf, max $R_{th(j-c)}$ Valid for switching of above 10kHz, excluding D.C. curve.

Fig.8*4 Typical peak forward current derating curve I_P - T_c (Not guaranteed)

Case Temperature : T_c [°C]

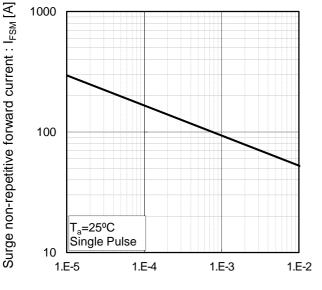


Case Temperature : T_c [°C] *4 Based on typ Vf, typ R_{th(j-c)} Typical value, not guaranteed Valid for switching of above 10kHz, excluding D.C. curve

Peak Forward Current : IP [A]

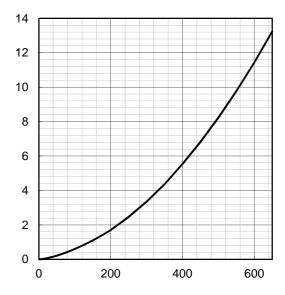
Electrical characteristic curves

Fig.9 Surge non-repetitive forward current vs. Pulse width (Sinusoidal waveform)



Pulse Width: PW [s]

Fig.10 Typical capacitance store energy

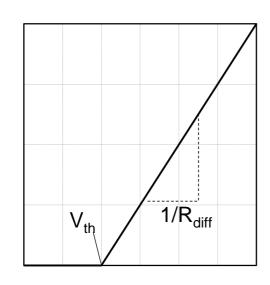


Capacitance stored energy : $\mathsf{E}_{_{\mathrm{C}}}[\mu \mathsf{J}]$

Reverse Voltage: V_R [V]

Symplified forward characteristic model

Fig.11 Equivalent forward current curve



Forward Voltage: V_F

$$V_F = V_{th} + R_{diff} I_F$$

$$V_{th} (T_j) = a_0 + a_1 T_j$$

 $R_{diff} (T_j) = b_0 + b_1 T_j + b_2 T_j^2$

Symbol	Typical Value	Unit
a ₀	9.35E-01	V
a ₁	-1.12E-03	V/°C
b ₀	2.65E-02	Ω
b ₁	6.80E-05	Ω/°C
b ₂	7.20E-07	$\Omega/^{\circ}C^{2}$

 T_i in °C; -55 °C < T_i < °C; I_F < 30 A

Forward Current: IF

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